

# 2SK3523-01R

FUJI POWER MOSFET

Super FAP-G Series

N-CHANNEL SILICON POWER MOSFET

### Features

- High speed switching
- Low on-resistance
- No secondary breakdown
- Low driving power
- Avalanche-proof

### Applications

- Switching regulators
- UPS (Uninterruptible Power Supply)
- DC-DC converters

### Maximum ratings and characteristic Absolute maximum ratings

(Tc=25°C unless otherwise specified)

Item	Symbol	Ratings	Unit	
Drain-source voltage	V <sub>DS</sub>	500	V	
	V <sub>DSX</sub> *5	500	V	
Continuous drain current	I <sub>D</sub>	±21	A	
Pulsed drain current	I <sub>D(puls)</sub>	±84	A	
Gate-source voltage	V <sub>GS</sub>	±30	V	
Repetitive or non-repetitive	I <sub>AR</sub> *2	21	A	
Maximum Avalanche Energy	E <sub>AS</sub> *1	400	mJ	
Maximum Drain-Source dV/dt	dV <sub>DS</sub> /dt *4	20	kV/μs	
Peak Diode Recovery dV/dt	dV/dt *3	5	kV/μs	
Max. power dissipation	P <sub>D</sub>	T <sub>a</sub> =25°C	3.125	W
		T <sub>c</sub> =25°C	120	
Operating and storage temperature range	T <sub>ch</sub>	+150	°C	
	T <sub>stg</sub>	-55 to +150	°C	
Isolation Voltage	V <sub>ISO</sub> *6	2	kVrms	

\*1 L=1.67mH, V<sub>CC</sub>=50V \*2 T<sub>ch</sub>≤150°C \*3 I<sub>F</sub>≤-I<sub>D</sub>, -di/dt=50A/μs, V<sub>CC</sub>≤BV<sub>DSS</sub>, T<sub>ch</sub>≤150°C

\*4 V<sub>DS</sub>≤500V \*5 V<sub>GS</sub>=-30V \*6 t=60sec f=60Hz

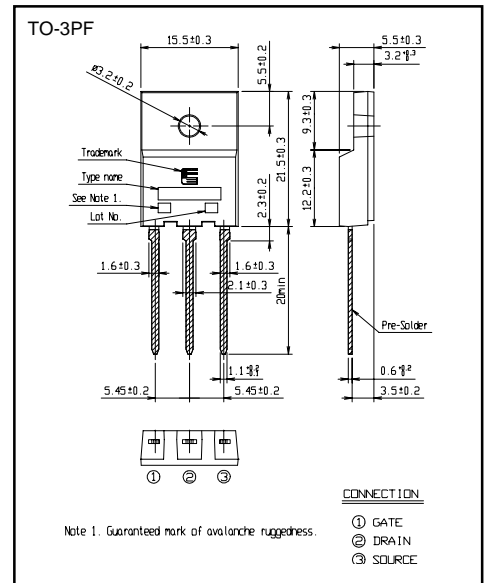
### Electrical characteristics (Tc =25°C unless otherwise specified)

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =250μA V <sub>GS</sub> =0V	500			V
Gate threshold voltage	V <sub>GS(th)</sub>	I <sub>D</sub> =250μA V <sub>DS</sub> =V <sub>GS</sub>	3.0		5.0	V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> =500V V <sub>GS</sub> =0V			25	μA
		V <sub>DS</sub> =400V V <sub>GS</sub> =0V			250	
Gate-source leakage current	I <sub>GSS</sub>	V <sub>GS</sub> =±30V V <sub>DS</sub> =0V		10	100	nA
Drain-source on-state resistance	R <sub>DS(on)</sub>	I <sub>D</sub> =10.5A V <sub>GS</sub> =10V		0.20	0.26	Ω
Forward transconductance	g <sub>fs</sub>	I <sub>D</sub> =10.5A V <sub>DS</sub> =25V	11	22		S
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> =25V		2280	3420	pF
Output capacitance	C <sub>oss</sub>	V <sub>GS</sub> =0V		320	480	
Reverse transfer capacitance	C <sub>rss</sub>	f=1MHz		16	24	
Turn-on time t <sub>on</sub>	td(on)	V <sub>CC</sub> =300V I <sub>D</sub> =10.5A		27	41	ns
	t <sub>r</sub>	V <sub>GS</sub> =10V		37	56	
Turn-off time t <sub>off</sub>	td(off)	R <sub>GS</sub> =10 Ω		75	113	
	t <sub>f</sub>			11	17	
Total Gate Charge	Q <sub>G</sub>	V <sub>CC</sub> =300V		54	81	nC
Gate-Source Charge	Q <sub>GS</sub>	I <sub>D</sub> =21A		16	24	
Gate-Drain Charge	Q <sub>GD</sub>	V <sub>GS</sub> =10V		20	30	
Avalanche capability	I <sub>AV</sub>	L=1.67mH T <sub>ch</sub> =25°C	21			A
Diode forward on-voltage	V <sub>SD</sub>	I <sub>F</sub> =21A V <sub>GS</sub> =0V T <sub>ch</sub> =25°C		0.98	1.50	V
Reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> =21A V <sub>GS</sub> =0V		0.7		μs
Reverse recovery charge	Q <sub>rr</sub>	-di/dt=100A/μs T <sub>ch</sub> =25°C		10.0		μC

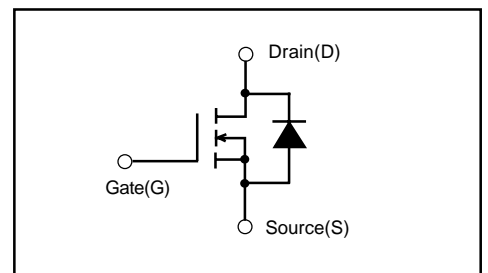
### Thermal characteristics

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	R <sub>th(ch-c)</sub>	channel to case			1.042	°C/W
	R <sub>th(ch-a)</sub>	channel to ambient			40.0	°C/W

### Outline Drawings



### Equivalent circuit schematic



■ Characteristics

